

TOSHIBA**TFR1N, TFR1T**

TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

TFR1N, TFR1T

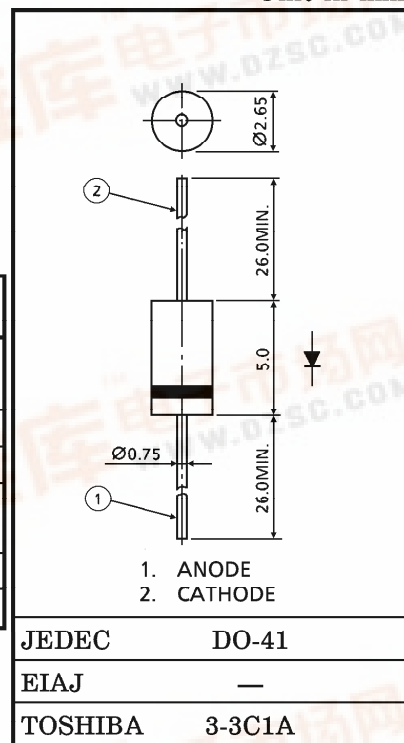
STROBO FLASHER APPLICATIONS. (FAST RECOVERY)

Unit in mm

- Average Forward Current : $I_F (AV) = 0.5A$
- Repetitive Peak Reverse Voltage : $V_{RRM} = 1000, 1500V$
- Reverse Recovery Time : $t_{rr} = 10\mu s$

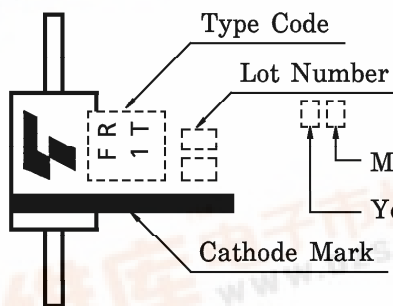
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	TFR1N	1000	V
	TFR1T	1500	
Average Forward Current	$I_F (AV)$	0.5	A
I^2t Limit Value ($t=1\sim 10ms$)	I^2t	2	A^2s
Peak One Cycle Surge Forward Current (Non Repetitive)	I_{FSM}	20	A
Junction Temperature	T_j	$-40\sim 125$	$^{\circ}C$
Storage Temperature Range	T_{stg}	$-40\sim 125$	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS** ($T_a = 25^{\circ}C$)

Weight : 0.3g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM} = 0.5A$	—	—	1.3	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = \text{Rated}$	—	—	10	μA
Reverse Recovery Time	t_{rr}	$I_F = 20mA, I_R = 1mA$	—	—	10	μs

MARKING

Color : Yellow

CODE	TYPE
FR1N	TFR1N
FR1T	TFR1T

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TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

